

Form PTO-139

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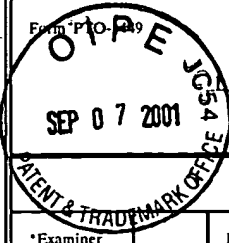
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M122-1568

SERIAL NO.
09879,335

APPLICANT Vishnu K. Agarwal, et al.

FILING DATE
June 11, 2001

GROUP
2813



LIST OF ART CITED BY APPLICANT
(Use several sheets if necessary)

U.S. PATENT DOCUMENTS

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
YK	AA 5,786,248	07/1998	Schuegraf			
	AB 3,571,914	03/1971	Lands, et al.			
	AC 4,464,701	08/1984	Roberts et al.			
	AD 5,504,041	04/1996	Summerfelt			
	AE 5,471,364	11/1995	Summerfelt et. al.			
	AF 5,654,222	08/1997	Sandhu et. al.			
	AG 5,663,088	09/1997	Sandhu et. al.			
	AH 5,442,213	08/1995	Okudaira			
	AI 5,910,880	06/1999	DeBoer et. al.			
	AJ 5,843,830	12/1998	Graettinger et. al.			
	AK 5,854,107	12/1998	Park et al.			
YK	AL 5,622,883	04/1997	Kim			

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
YK	AM 7611928	3/77	Netherlands				X
	AN						

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

YK	AQ	Kamiyama, Satoshi et al., "Ultrathin Tantalum Oxide Capacitor Dielectric Layers Fabricated Using Rapid Thermal Nitridation Prior to Low Pressure Chemical Vapor Deposition: J. Electrochem. Soc., Vol. 140, #6, pp 1618-25 (6/1993)
	AP	Yoshimaru, M., et al., "High Quality Ultra Thin SiO ₂ N ₂ Film Selectively Deposited on Poly-Si Electrode by LPCVD with <i>In Situ</i> HF Vapor Cleaning", <i>IEEE</i> , pp. 271-274 (04/1992)
	AQ	Kamiyama, S., et al., Highly Reliable 2.5 nm Ta ₂ O ₅ Capacitor Process Technology for 256 Mbit DRAMs", <i>IEEE</i> , pp. 827-830 (9/1991)
YK	AR	Eimori, T., et al., "A Newly Designed Planar Stacked Capacitor Cell with high Dielectric Constant Film for 256Mbit DRAM", 1993 <i>IEEE</i> , pp. 631-634.

EXAMINER *YK* DATE CONSIDERED 3/18/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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ATTY. DOCKET NO.
MI22-1568

SERIAL NO.
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LIST OF ART CITED BY APPLICANT
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APPLICANT Kunal R. Parekh, et al.

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June 11, 2001

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2815

U.S. PATENT DOCUMENTS

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
YJA	AA 5,597,756 ✓	01/1997	Fazan et al.			
	AB 5,843,818 ✓	12/1998	Joo et al.			
	AC 5,866,453 ✓	02/1999	Prall et al.			
	AD 5,488,011 ✓	01/1996	Fiura et al.			
	AE 5,405,796 ✓	04/1995	Jones			
	AF 5,346,844 ✓	09/1994	Cho			
	AG 5,352,623 ✓	10/1994	Kamiyama			
	AH 5,438,012 ✓	08/1995	Kamiyama			
YJA	AI 5,893,980 ✓	04/1999	Cho			
	AJ					
	AK					
	AL					

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YJA	AO	Fazan, P.C., et. al., "A High-C Capacitor (20.4fF/μm ²) with Ultrathin CVD-Ta ₂ O ₅ Films Deposited on Rugged Poly-Si for High Density DRAMS", 1992 IEEE, pp. 263-266.
	AP	Lesacherre, P-Y, et. al., "A Gbit-Scale DRAM Stacked Capacitor Technology with ECR MOCVD SrTiO ₃ and RIE Patterned RuO ₂ /TiN Storage Nodes", 1994 IEEE, pp. 831-834.
YJA	AQ	Yamaguchi, H., et. al., "Structural and Electrical Characterization of SrTiO ₃ Thin Films Prepared by Metal Organic Chemical Vapor Deposition", Jpn. J. Appl. Phys. Vol. 32 (1993), Pt. 1, No. 9B, pp. 4069-4073.
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EXAMINER

YJA

DATE CONSIDERED

8/8/02

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